



August 2016

MCT6, MCT61, MCT62

8-Pin Dual Channel Phototransistor Optocouplers

Features

- Two Isolated Channels Per Package
- Safety and Regulatory Approvals:
 - UL1577, 5,000 VAC_{RMS} for 1 Minute
 - DIN-EN/IEC60747-5-5, 890 V Peak Working Insulation Voltage

Applications

- AC line/digital logic – isolate high voltage transients
- Digital logic/digital logic – eliminate spurious grounds
- Digital logic/AC triac control – isolate high voltage transients
- Twisted pair line receiver – eliminate ground loop feedthrough
- Telephone/telegraph line receiver – isolate high voltage transients
- High frequency power supply feedback control – maintain floating grounds and transients
- Relay contact monitor – isolate floating grounds and transients
- Power supply monitor – isolate transients

Description

The general purpose optocouplers, MCT6, MCT61, and MCT62, have two isolated channels in a standard plastic 8-pin dual-in-line (DIP) package for density applications. Each channel consists of a gallium arsenide infrared emitting diode driving a NPN silicon planar phototransistor. For four channel applications, two packages fit into a standard 16-pin DIP socket.

Functional Schematic

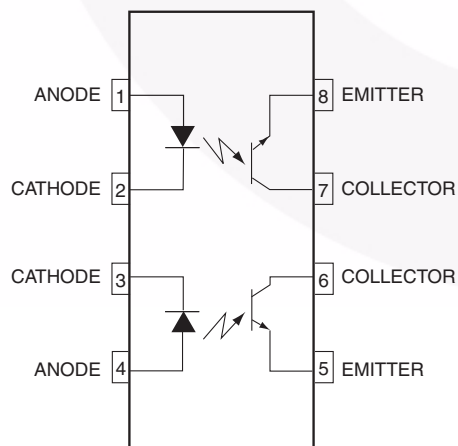


Figure 1. Schematic

Package Outlines

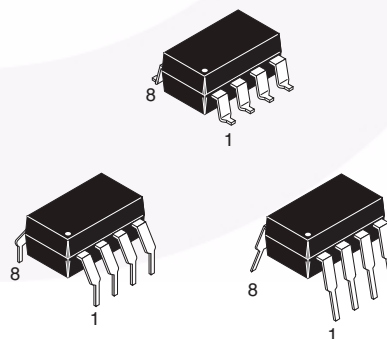


Figure 2. Package Outlines

Safety and Insulation Ratings

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for “safe electrical insulation” only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter		Characteristics
Installation Classifications per DIN VDE 0110/1.89 Table 1, For Rated Mains Voltage	< 150 V _{RMS}	I–IV
	< 300 V _{RMS}	I–IV
Climatic Classification		55/115/21
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
V _{PR}	Input-to-Output Test Voltage, Method A, V _{IORM} × 1.6 = V _{PR} , Type and Sample Test with t _m = 10 s, Partial Discharge < 5 pC	1424	V _{peak}
	Input-to-Output Test Voltage, Method B, V _{IORM} × 1.875 = V _{PR} , 100% Production Test with t _m = 1 s, Partial Discharge < 5 pC	1668	V _{peak}
V _{IORM}	Maximum Working Insulation Voltage	890	V _{peak}
V _{IOTM}	Highest Allowable Over-Voltage	8000	V _{peak}
	External Creepage	≥ 7	mm
	External Clearance	≥ 7	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.4	mm
T _S	Case Temperature ⁽¹⁾	175	°C
I _{S,INPUT}	Input Current ⁽¹⁾	60	mA
P _{S,OUTPUT}	Output Power ⁽¹⁾	150	mW
R _{IO}	Insulation Resistance at T _S , V _{IO} = 500 V ⁽¹⁾	> 10 ⁹	Ω

Note:

1. Safety limit values – maximum values allowed in the event of a failure.

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. $T_A = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	Value	Unit
T_{STG}	Storage Temperature	-55 to +150	$^\circ\text{C}$
T_{OPR}	Operating Temperature	-55 to +100	$^\circ\text{C}$
T_J	Junction Temperature	-55 to +125	$^\circ\text{C}$
T_{SOL}	Lead Solder Temperature	260 for 10 seconds	$^\circ\text{C}$
P_D	Total Device Power Dissipation @ $T_A = 25^\circ\text{C}$	400	mW
	Derate Above 25°C	5.33	mW/ $^\circ\text{C}$
EMITTER (Each channel)			
I_F	DC / Average Forward Input Current	60	mA
$I_{F(\text{pk})}$	Forward Current - Peak (PW = 1 μs , 300pps)	3	A
V_R	Reverse Input Voltage	3	V
$P_{D(\text{EMITTER})}$	Total Power Dissipation @ $T_A = 25^\circ\text{C}$	100	mW
	Derate Above 25°C	1.3	mW/ $^\circ\text{C}$
DETECTOR			
I_C	Continuous Collector Current	30	mA
$P_{D(\text{DETECTOR})}$	Total Power Dissipation @ $T_A = 25^\circ\text{C}$	150	mW
	Derate Above 25°C	2.0	mW/ $^\circ\text{C}$

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise specified.

Individual Component Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
EMITTER						
V_F	Input Forward Voltage	$I_F = 20\text{ mA}$		1.2	1.5	V
V_R	Reverse Voltage	$I_R = 10\text{ }\mu\text{A}$	3	25		V
I_R	Reverse Leakage Current	$V_R = 5\text{ V}$		0.001	10	μA
C_J	Junction Capacitance	$V_F = 0\text{ V}$, $f = 1\text{ MHz}$		50		pF
DETECTOR						
BV_{CEO}	Collector-to-Emitter Breakdown Voltage	$I_C = 1.0\text{ mA}$, $I_F = 0$	30	85		V
BV_{ECO}	Emitter-to-Collector Breakdown Voltage	$I_E = 100\text{ }\mu\text{A}$, $I_F = 0$	6	13		V
I_{CEO}	Collector-to-Emitter Dark Current	$V_{CE} = 10\text{ V}$, $I_F = 0$		5	100	nA
C_{CE}	Capacitance	$V_{CE} = 0\text{ V}$, $f = 1\text{ MHz}$		8		pF

Transfer Characteristics

Symbol	Parameter	Device	Test Conditions	Min.	Typ.	Max.	Unit
DC CHARACTERISTICS							
CTR	Current Transfer Ratio, Collector-to-Emitter	MCT6	$I_F = 10\text{ mA}$, $V_{CE} = 10\text{ V}$	20			%
		MCT61	$I_F = 5\text{ mA}$, $V_{CE} = 5\text{ V}$	50			
		MCT62		100			
$V_{CE(SAT)}$	Saturation Voltage, Collector-to-Emitter	ALL	$I_F = 16\text{ mA}$, $I_C = 2\text{ mA}$		0.15	0.4	V

AC CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Non-Saturated						
T _{ON}	Turn-On Time	R _L = 100 Ω, I _C = 2 mA, V _{CC} = 10 V		3.0		μs
T _{OFF}	Turn-Off Time			3.0		μs
T _R	Rise Time			2.4		μs
T _F	Fall Time			2.4		μs
Saturated						
T _{ON}	Turn-On Time	I _F = 16 mA, R _L = 1.9 kΩ, V _{CE} = 5 V		2.4		μs
T _{OFF}	Turn-Off Time			25.0		μs

Isolation Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_{ISO}	Input-Output Isolation Voltage	$I_{I-O} \leq 10\text{ }\mu\text{A}$, $t = 1\text{ Minute}$	5,000			$V_{AC(RMS)}$
C_{ISO}	Isolation Capacitance	$f = 1\text{ MHz}$		0.5		pF
R_{ISO}	Isolation Resistance	$V_{I-O} = 500\text{ VDC}$	10^{11}			Ω

Typical Performance Curves

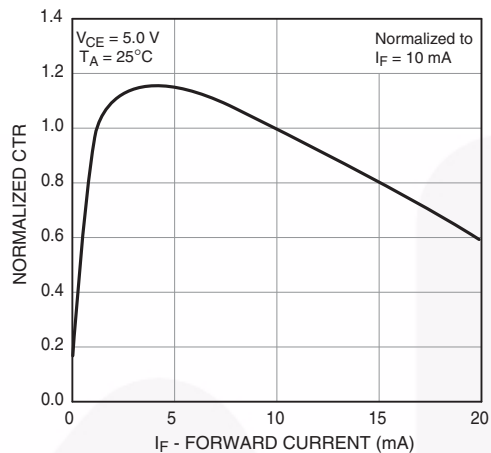


Fig. 3 Normalized CTR vs. Forward Current

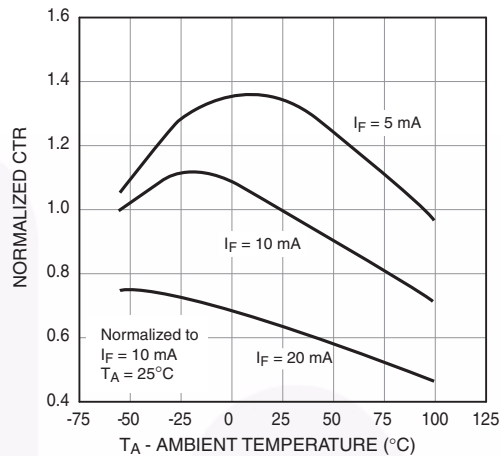


Fig. 4 Normalized CTR vs. Ambient Temperature

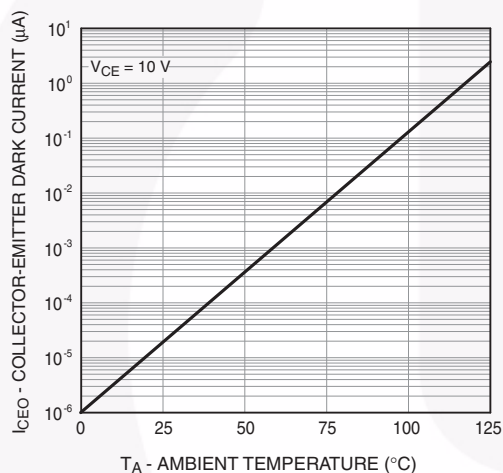


Fig. 5 Dark Current vs. Ambient Temperature

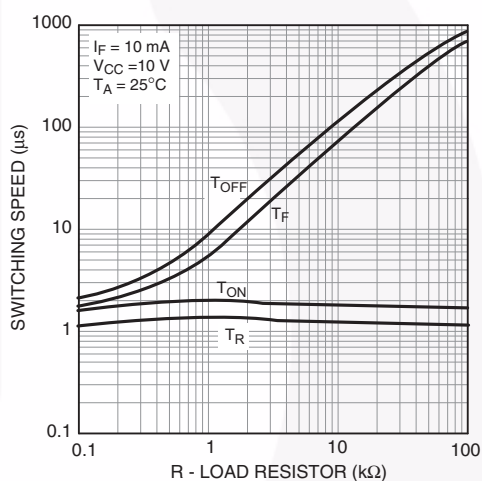


Fig. 6 Switching Speed vs. Load Resistor

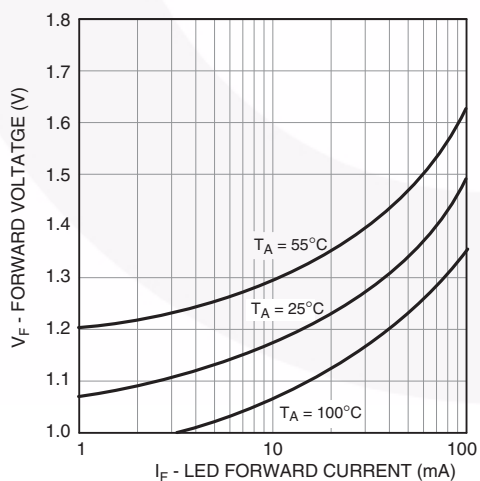


Fig. 7 LED Forward Voltage vs. Forward Current

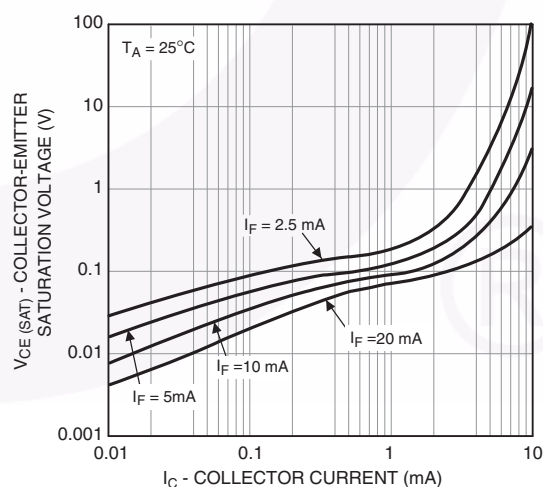


Fig. 8 Collector-Emitter Saturation Voltage vs. Collector Current

Switching Time Test Circuit and Waveforms

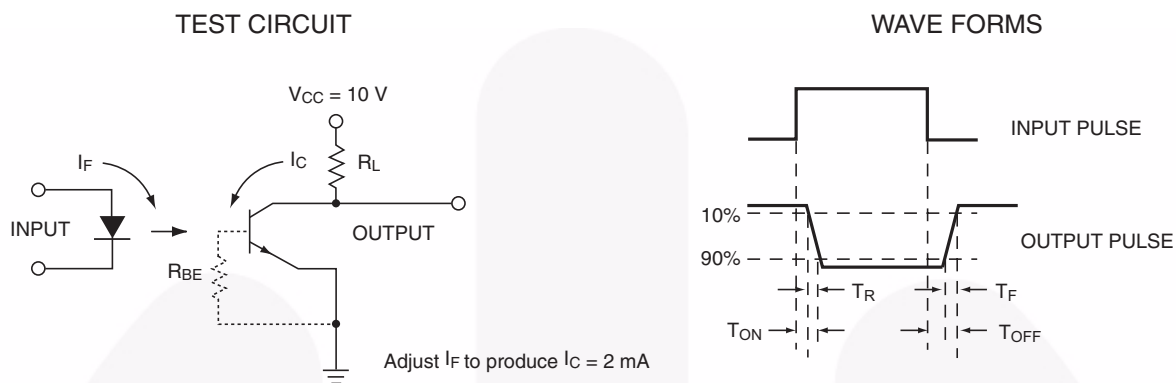
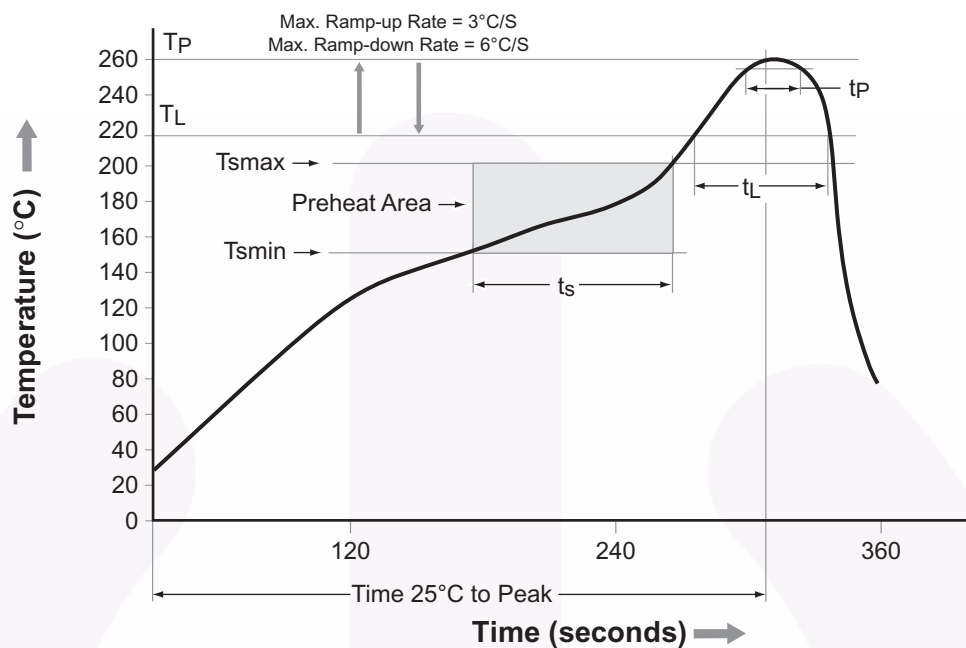


Figure 9. Switching Time Test Circuit and Waveforms

Reflow Profile



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T _{smin})	150°C
Temperature Max. (T _{smax})	200°C
Time (t _s) from (T _{smin} to T _{smax})	60–120 seconds
Ramp-up Rate (t _L to t _p)	3°C/second max.
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60–150 seconds
Peak Body Package Temperature	260°C +0°C / –5°C
Time (t _p) within 5°C of 260°C	30 seconds
Ramp-down Rate (T _p to T _L)	6°C/second max.
Time 25°C to Peak Temperature	8 minutes max.

Ordering Information

Part Number	Package	Packing Method
MCT6	DIP 8-Pin	Tube (50 units per tube)
MCT6S	SMT 8-Pin (Lead Bend)	Tube (50 units per tube)
MCT6SD	SMT 8-Pin	Tape and Reel (1,000 units per reel)
MCT6300	DIN EN/IEC 60747-5-5 Option	Tube (50 units per tube)
MCT63S	SMT 8-Pin (Lead Bend); DIN EN/IEC 60747-5-5 Option	Tube (50 units per tube)
MCT63SD	SMT 8-Pin; DIN EN/IEC 60747-5-5 Option	Tape and Reel (1,000 units per reel)
MCT6300W	0.4" Lead Spacing; DIN EN/IEC 60747-5-5 Option	Tube (50 units per tube)

Note

- The product orderable part number system listed in this table also applies to the MCT61 and MCT62.

Marking Information

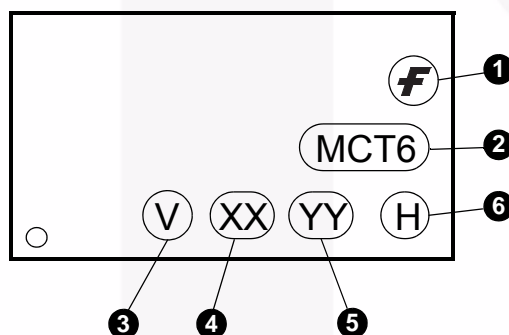
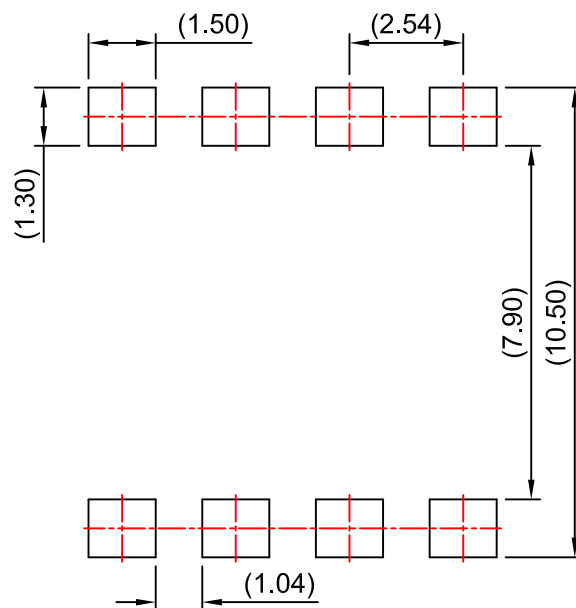
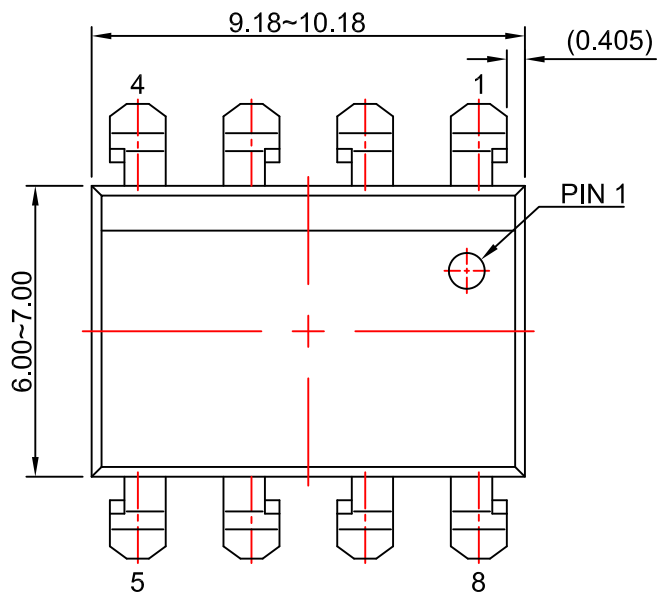


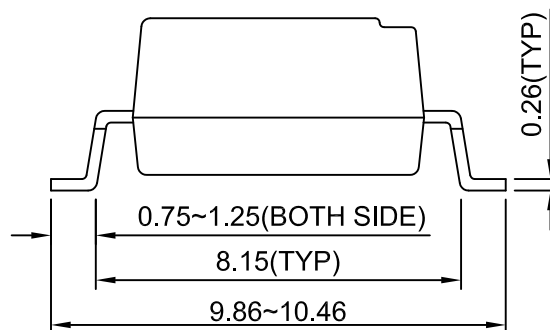
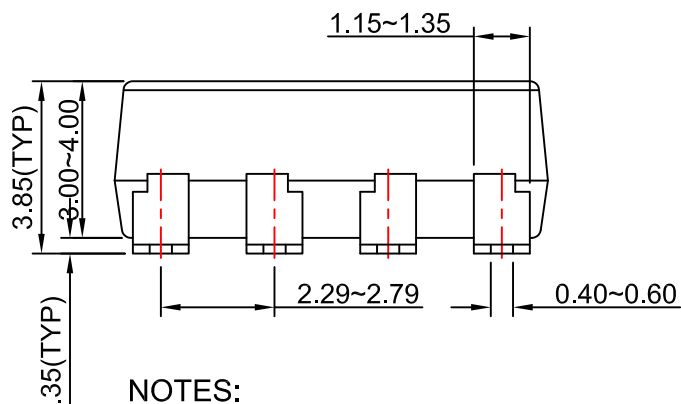
Figure 10. Top Mark

Table 1. Top Mark Definitions

1	Fairchild Logo
2	Device Number
3	DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option)
4	Two-Digit Year Code, e.g., "16"
5	Digit Work Week, Ranging from "01" to "53"
6	Assembly Package Code



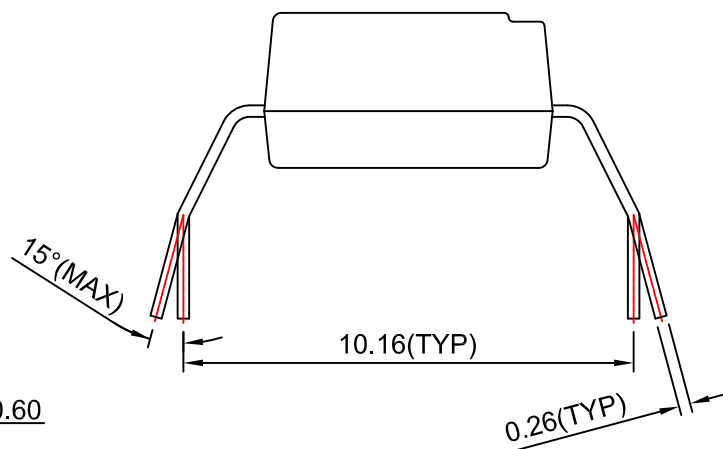
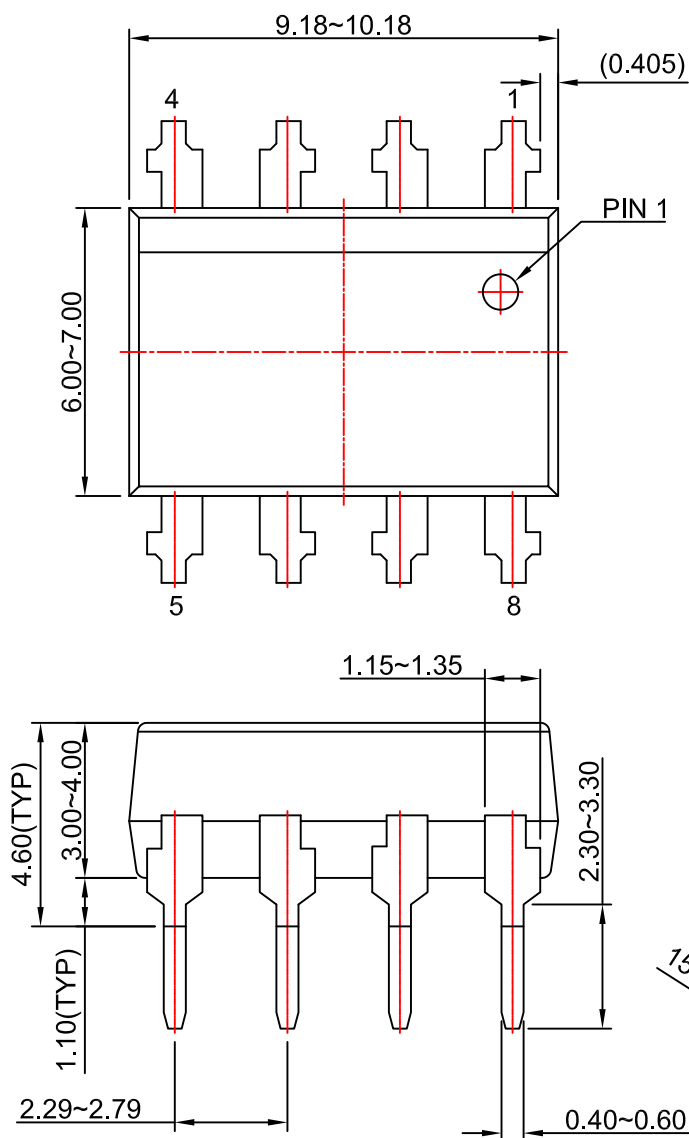
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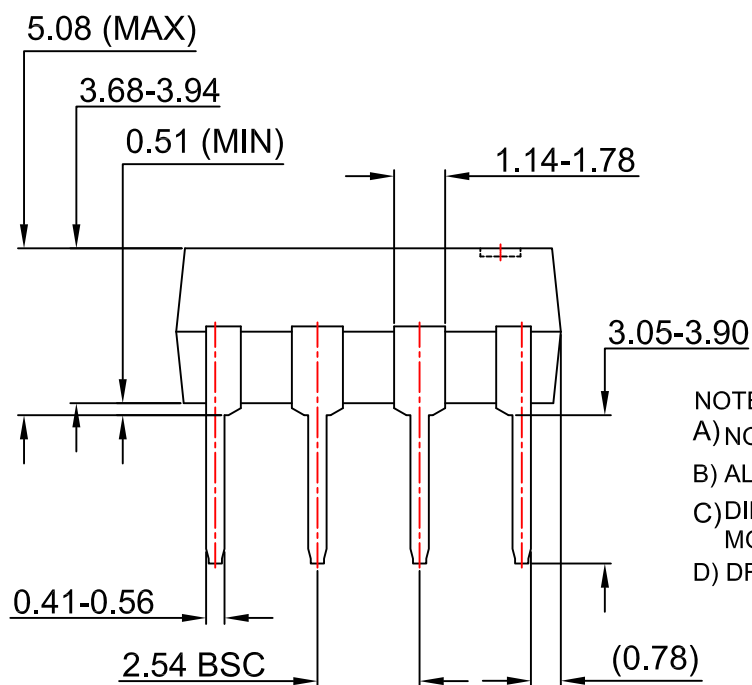
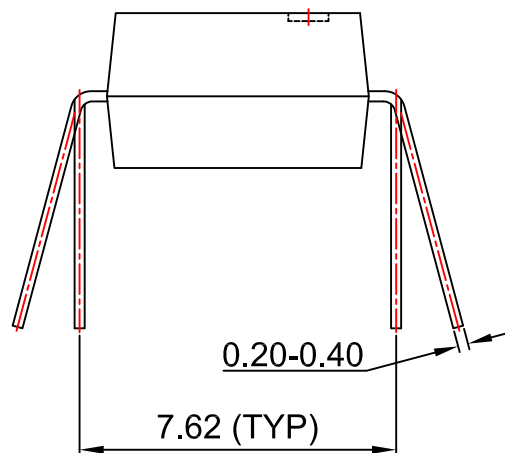
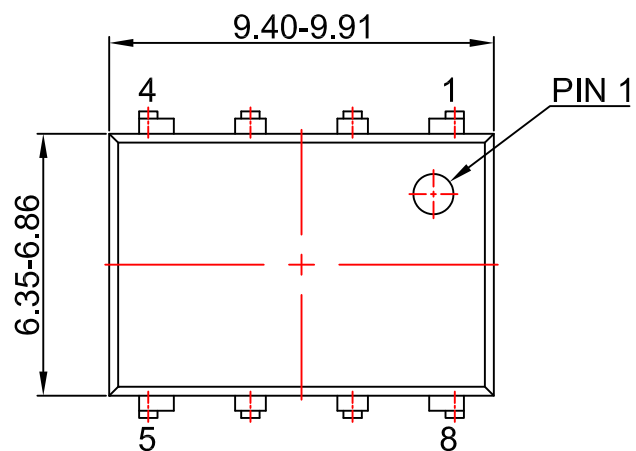




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